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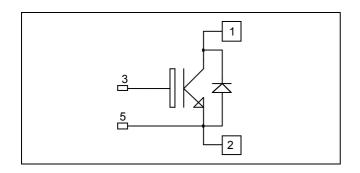
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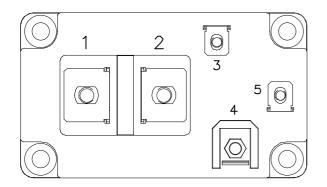
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Single switch Trench + Field Stop IGBT4 Power Module





APTGL700U120D4G

$V_{CES} = 1200V$ $I_{C} = 700A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- M6 connectors for power
- M4 connectors for signal
- High level of integration

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
I _C	Continuous Collector Current	$T_C = 25^{\circ}C$	910	
	Continuous Conector Current	$T_C = 80^{\circ}C$	700	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	1800	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	3000	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	1200A@1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com APTGL700U120D4G - Rev 2 October 2012

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All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$; $V_{CE} = 1200V$				4	mA
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 600A$	$T_j = 25^{\circ}C$ $T_i = 150^{\circ}C$		1.8	2.2	V
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 24 \text{ mA}$		5	5.8	6.5	V

Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			37.2		
C _{oes}	Output Capacitance	$V_{CE} = 25V$			2.3		nF
C _{res}	Reverse Transfer Capacitance	f = 1 MHz	f = 1MHz		2.04		
Q _G	Gate charge	V_{GE} = -8V / 15V ; V_{CE} =600V I _C =600A			3.4		μC
T _{d(on)}	Turn-on Delay Time	Inductive Switch	hing (25°C)		160		ns
Tr	Rise Time	$V_{GE} = \pm 15V$			30		
T _{d(off)}	Turn-off Delay Time	$V_{CE} = 600V$ $I_{C} = 600A$			340		
T _f	Fall Time	$R_{G} = 1.8\Omega$			80		
T _{d(on)}	Turn-on Delay Time		Inductive Switching (150°C)		170		ns
Tr	Rise Time	$V_{GE} = \pm 15V$ $V_{CE} = 600V$			40		
T _{d(off)}	Turn-off Delay Time	$I_{\rm C} = 600 {\rm A}$	-		450		
T _f	Fall Time	$R_G = 1.8\Omega$			170		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$	$T_{J} = 150^{\circ}C$		66		mJ
E _{off}	Turn-off Switching Energy	$I_{\rm C} = 600 \text{A}$ $R_{\rm G} = 1.8 \Omega$	$T_J = 150^{\circ}C$		66		mJ
I _{sc}	Short Circuit data	$\begin{array}{l} V_{GE} \leq \!\! 15V \ ; \ V_{Bus} = 900V \\ t_p \leq 10 \mu s \ ; \ T_j = 150^\circ C \end{array}$			2400		А

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Repetitive Reverse Voltage			1200			V
I _{RRM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$			250 2000	μΑ
I _F	DC Forward Current		$T_C = 80^{\circ}C$		600		А
V _F	Diode Forward Voltage	$I_{\rm F} = 600 {\rm A}$ $V_{\rm GE} = 0 {\rm V}$	$T_j = 25^{\circ}C$		1.7	2.2	v
• F			$T_{j} = 150^{\circ}C$		1.65		
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		155		ns
urr	Reverse Recovery Time	I = 600 A	$T_{j} = 150^{\circ}C$		300		115
0	Reverse Recovery Charge	$I_{\rm F} = 600 {\rm A}$ $V_{\rm R} = 600 {\rm V}$ $di/dt = 7000 {\rm A}/\mu {\rm s}$	$T_j = 25^{\circ}C$		53		чС
Q _{rr}			$T_{j} = 150^{\circ}C$		110		μC
E _{rr}	Reverse Recovery Energy		$T_j = 25^{\circ}C$		23.5		mJ
	Reverse Receivery Energy		$T_{j} = 150^{\circ}C$		46		1115

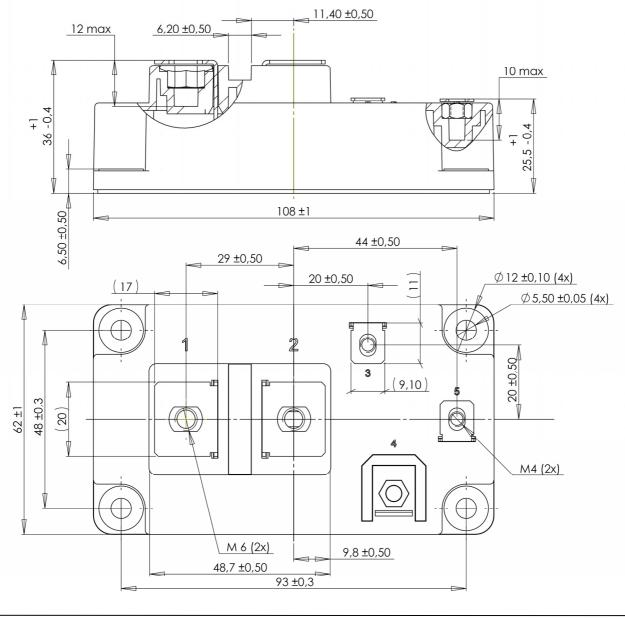


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Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance	IGBT			0.05	°C/W	
R _{th} JC		Diode			0.1	C/ W	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		4000			V	
T _J	Operating junction temperature range		-40		175	°C	
T _{STG}	Storage Temperature Range		-40		125		
T _C	Operating Case Temperature		-40		125		
Torque	Mounting torque	M6	3		5	N.m	
		M4	1		2	19.111	
Wt	Package Weight				350	g	

D4 Package outline (dimensions in mm)

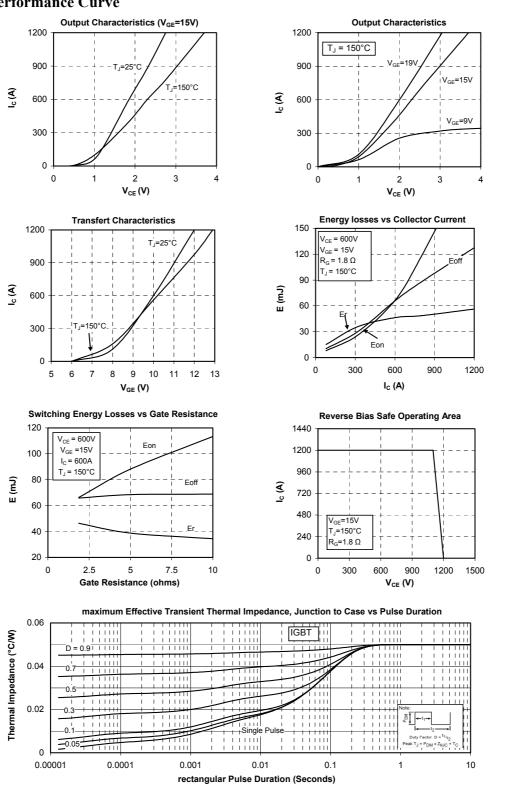


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Typical Performance Curve





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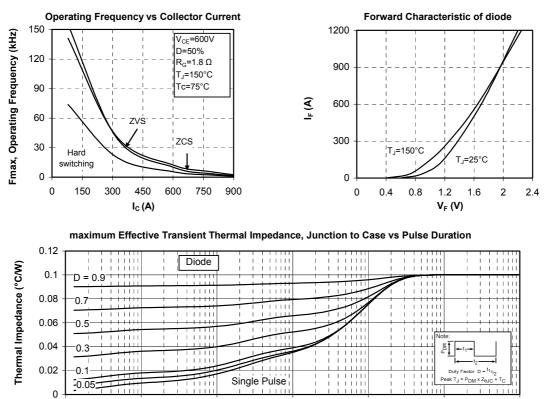


0.00001

0.0001

0.001

APTGL700U120D4G



0.01

Rectangular Pulse Duration in Seconds

0.1

1

10

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